FORM PTO-1449  INFORMATION DISCLOSURE  CITATION IN AN APPLICATION				DOCKET NUMBER APPLICATION NUMBER 0629			
				APPLICANT Mark Albert Crowder			
				FILING DATE: November 8, 2001	GROUP ART UNIT		
U.S. PATENT DOCUMENTS							
EXAMINER	DOCUMENT	DATE		NAME	CLASS	SUB	FIL. DATE
INITIAL	NUMBER	01/00/01	ļ <u>,                                     </u>		120	CLASS	IF APPROP.
SDF	6,177,301	01/23/01	Jung		438	150	05/13/99
SDF	6,235,614	05/22/01	Yang		438	486	05/13/99
SDE	6,274,888	08/14/01	Suzuki et al.		257	72	01/10/00
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FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	]	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO
	NOMBER					02,7100	125
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OTHER DOCUMENTS							
SDI	Article entitled, "Phase Transformation Mechanisms involved in Excimer Laser crystallization of Amorphous Silicon Films", by Im et al., published in Appl. Phys. Lett. 63 (14), 4 October 1993, pp 1969-1971						
SOI	Article entitled, "Sequential Lateral Solidification of Thin Silicon Films on SiO <sub>2</sub> ", by Sposili et al., published in Appl. Phys. Lett. 69 (19) 4 November 1996, pp 2864-2866						
SDI	Article entitled, "Controlled Super-Lateral Growth of Si Films for Microstructural Manipulation and Optimization", by Im et al., published in Phys. Stat. Sol. (a) 166, 603 (1998), pp 603-617						
SOI	Article entitled, "Crystalline Si Films for Integrated Active-Matrix Liquid-Crystal Displays", by Im et al., published in MRS Bulletin/ March 1996, pp 39-48						
SOF	Article entitled, "Low-Temperature Single-Crystal Si TFT's Fabricated on Si Films Processed via Sequential Lateral Solidification", by Crowder et al., published in IEEE Electron Device Letters, Vol. 19, No. 8, August 1998, pp 306-308						
SDI	Article entitled, "Single-Crystal Si Films for Thin-Film Transistor Devices", by Im et al., published in Appl. Phys. Lett. 70 (25), 23 June 1997, pp 34343436						
EXAMINER Star Andrew				DATE CONSIDERED 2/22/04			